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What is claimed is:

1. A method for manufacturing a semiconductor device comprising:

forming an N region and P region on a substrate, forming wiring so as to connect one or both of these N and P regions; and

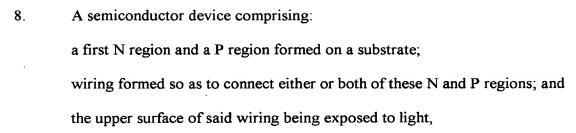
performing a processing step on a semiconductor substrate on which the upper surface of said wiring is exposed using a liquid,

wherein said processing step is performed in a state in which the wavelength of light radiated onto said semiconductor substrate is 500 nm to less than 1 μ m.

- 2. A method according to claim 1, wherein said processing step is performed in a state in which said semiconductor substrate is grounded.
- 3. A method according to claim for 2, wherein said processing step is a cleaning step performed during, before or after a step that includes chemical mechanical polishing (CMP) for forming said wiring.
- 4. A processing system comprising a processing unit that processes a semiconductor substrate using a liquid and a light source.
- 5. A processing system according to claim 4, wherein said light source radiates light having a wavelength of 500nm to less than 1 µm onto said processing unit.
- 6. A processing system according to claim 4, wherein said processing unit provided with a rotating section that holds and rotates a semiconductor substrate, and a liquid supply section that supplies liquid to said semiconductor substrate, and said rotating section being grounded.
- 7. A processing system according to claim 5, wherein said processing unit provided with a rotating section that holds and rotates a semiconductor substrate, and a liquid supply section that supplies liquid to said semiconductor substrate, and said rotating section being grounded.



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- wherein a second N region is formed independent of said first N region on said substrate.
 - 9. A semiconductor device according to claim 8, wherein the total surface area of said first N region and said second N region is 100 to 1/100 times the total surface area of said P region.
 - 10. A semiconductor device according to claim 8, wherein said second N region is formed at the periphery of said substrate.
 - 11. A semiconductor device according to claim 8, wherein said wiring has any one of Cu, Al and W as its main component.

